

#### **60V PNP SMALL SIGNAL TRANSISTOR IN SOT23**

### **Features**

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Complementary NPN Type: MMBT2222AQ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The MMBT2907AQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

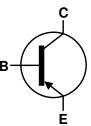
## **Mechanical Data**

- Package: SOT23
- Package Material: Molded Plastic, "Green" Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.008 grams (Approximate)

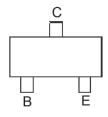








Device Symbol



Top View Pin-Out

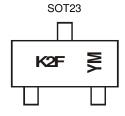
### Ordering Information (Note 4)

Product	Status	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMBT2907AQ-7-F	Active	Automotive	K2F	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



K2F = Product Type Marking Code YM = Date Code Marking

Y or  $\overline{Y}$  = Year (ex: I = 2021) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2013		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	Α		- 1	J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## Absolute Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	$V_{EBO}$	-6.0	V
Collector Current	Ic	-600	mA
Peak Collector Current	I <sub>CM</sub>	-800	mA
Peak Base Current	I <sub>BM</sub>	-200	mA

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit		
Collector Dower Discinstian	(Note 5)	0	310	m\\/	
Collector Power Dissipation	(Note 6)	P <sub>D</sub>	350	mW	
Thermal Resistance, Junction to Ambient	(Note 5)	0	403	°C/W	
Thermal nesistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	357	C/VV	
Thermal Resistance, Junction to Leads	(Note 7)	$R_{ heta JL}$	350	°C/W	
Thermal Resistance, Junction to Case (Note 5)		R <sub>eJC</sub>	120	°C/W	
Operating and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55 to +150	°C	

## ESD Ratings (Note 8)

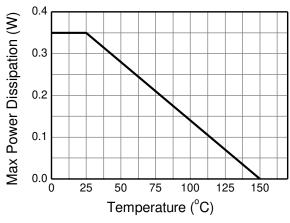
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

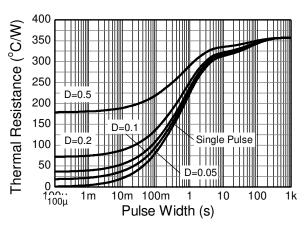
Notes:

- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air 5. For a device mounted of minimum recommended pad layout 102 copper that is conditions whilst operating in a steady-state.
  6. Same as Note 5, except the device is mounted on 15 mm x 15mm 1oz copper.
  7. Thermal resistance from junction to solder-point (at the end of the leads).
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



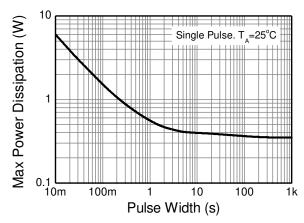
# **Thermal Characteristics and Derating Information**





**Derating Curve** 

**Transient Thermal Impedance** 



**Pulse Power Dissipation** 

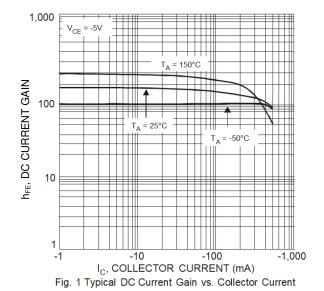


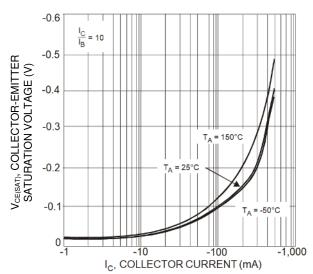
## Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

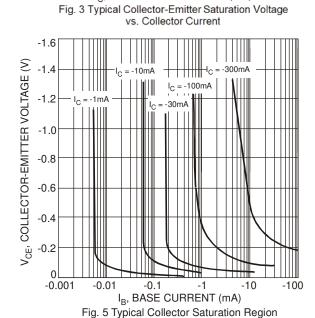
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	$BV_{CBO}$	-60	_	V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-60	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6.0	_	V	$I_E = -100\mu A, I_C = 0$
Collector Cut-Off Current	I <sub>CBO</sub>		-10	nA	V <sub>CB</sub> = -50V, I <sub>E</sub> = 0
	·CBO		-10	μA	$V_{CB} = -50V, I_E = 0, T_A = +125^{\circ}C$
Collector Cut-Off Current	I <sub>CEX</sub>	_	-50	nA	$V_{CE} = -30V, V_{EB(off)} = -0.5V$
Base Cut-Off Current	$I_{BL}$	_	-50	nA	$V_{CE} = -30V$ , $V_{EB(off)} = -0.5V$
Emitter Cut-Off Current	I <sub>EBO</sub>	_	-50	nA	V <sub>EB</sub> = -6.0V
ON CHARACTERISTICS (Note 9)					
DC Current Gain	h <sub>FE</sub>	75 100 100 100 50		_	$\begin{split} I_{C} &= -100 \mu A, \ V_{CE} = -10V \\ I_{C} &= -1.0 m A, \ V_{CE} = -10V \\ I_{C} &= -10 m A, \ V_{CE} = -10V \\ I_{C} &= -150 m A, \ V_{CE} = -10V \\ I_{C} &= -500 m A, \ V_{CE} = -10V \end{split}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	-0.4 -1.6	٧	$I_C = -150$ mA, $I_B = -15$ mA $I_C = -500$ mA, $I_B = -50$ mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	_	-1.3 -2.6	٧	$I_C = -150$ mA, $I_B = -15$ mA $I_C = -500$ mA, $I_B = -50$ mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_{obo}$	_	8.0	pF	$V_{CB} = -10V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	Cibo	_	30	pF	$V_{EB} = -2.0V$ , $f = 1.0MHz$ , $I_{C} = 0$
Current Gain-Bandwidth Product	f⊤	200	_	MHz	V <sub>CE</sub> = -20V, I <sub>C</sub> = -50mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Turn-On Time	t <sub>on</sub>	_	45	ns	1/ 00V I 450A
Delay Time	$t_d$	_	10	ns	$V_{CC} = -30V, I_C = -150mA,$ $I_{B1} = -15mA$
Rise Time	t <sub>r</sub>	_	40	ns	1011 - 10111/A
Turn-Off Time	t <sub>off</sub>	_	100	ns	V 00V 1 450mA
Storage Time	ts		80	ns	$V_{CC} = -6.0V, I_C = -150mA,$ $I_{B1} = -I_{B2} = -15mA$
Fall Time	t <sub>f</sub>	_	30	ns	10117

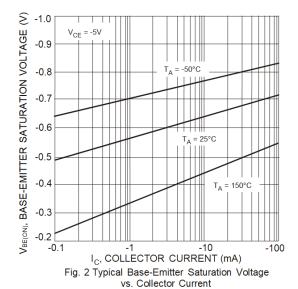
Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.











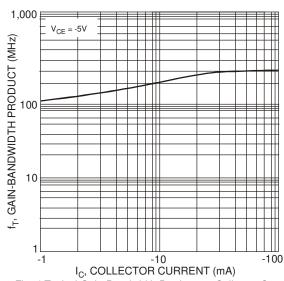


Fig. 4 Typical Gain-Bandwidth Product vs. Collector Current

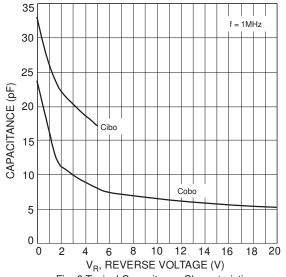


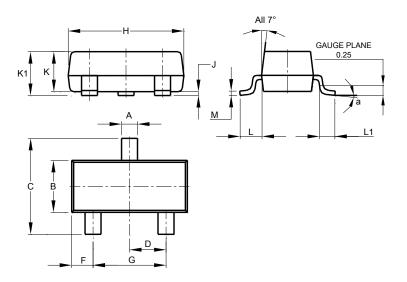
Fig. 6 Typical Capacitance Characteristics



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23

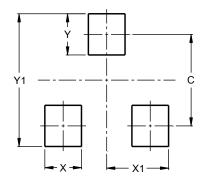


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All	Dimens	ions in	mm			

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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